Shin Mou

List of Publications by Year
in descending order

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22 papers	1,454 citations	567281 15 h-index	713466 21 g-index
22 all docs	22 docs citations	22 times ranked	1054 citing authors

#	Article	IF	Citations
1	Demonstration of high mobility and quantum transport in modulation-doped Î²-(AlxGa1-x)2O3/Ga2O3 heterostructures. Applied Physics Letters, 2018, 112, .	3.3	264
2	Donors and deep acceptors in Î²-Ga2O3. Applied Physics Letters, 2018, 113, .	3.3	203
3	Î²-Gallium oxide power electronics. APL Materials, 2022, 10, .	5.1	184
4	Ge-Doped ${eta }$ -Ga2O3 MOSFETs. IEEE Electron Device Letters, 2017, 38, 775-778.	3.9	165
5	Heteroepitaxy of N-type Î²-Ga2O3 thin films on sapphire substrate by low pressure chemical vapor deposition. Applied Physics Letters, 2016, 109, .	3.3	122
6	Lateral Î²-Ga₂O₃ field effect transistors. Semiconductor Science and Technology, 2020, 35, 013002.	2.0	85
7	Incomplete Ionization of a 110â€‰meV Unintentional Donor in Î²-Ga2O3 and its Effect on Power Devices. Scientific Reports, 2017, 7, 13218.	3.3	84
8	Towards Highâ€Mobility Heteroepitaxial Î²â€Ga₂O₃ on Sapphire â^' Dependence on The Substrate Offâ€Axis Angle. Physica Status Solidi (A) Applications and Materials Science, 2018, 215, 1700467.	1.8	84
9	MOCVD growth of high purity Ga2O3 epitaxial films using trimethylgallium precursor. Applied Physics Letters, 2020, 117, .	3.3	77
10	Adsorption-controlled growth of Ga2O3 by suboxide molecular-beam epitaxy. APL Materials, 2021, 9, .	5.1	38
11	Pulsed Power Performance of Î²-Gaâ„Oâ„ MOSFETs at L-Band. IEEE Electron Device Letters, 2020, 41, 989-992.	3.9	32
12	Toward high voltage radio frequency devices in Î²-Ga2O3. Applied Physics Letters, 2020, 117, .	3.3	23
13	Î³-phase inclusions as common structural defects in alloyed Î²-(AlxGa1â^'x)2O3 and doped Î²-Ga2O3 films. APL Materials, 2021, 9, .	5.1	23
14	Reduction of unintentional Si doping in Î²-Ga2O3 grown via plasma-assisted molecular beam epitaxy. Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films, 2020, 38, 043403.	2.1	20
15	Î²-Ga₂O₃ defect study by steady-state capacitance spectroscopy. Japanese Journal of Applied Physics, 2018, 57, 091101.	1.5	17
16	Si doping in MOCVD grown (010) Î²-(AlxGa1â^'x)2O3 thin films. Journal of Applied Physics, 2022, 131, .	2.5	15
17	Edge Doping Effect to the Surface Plasmon Resonances in Graphene Nanoribbons. Journal of Physical Chemistry C, 2019, 123, 19820-19827.	3.1	8
18	Microwave imaging of etching-induced surface impedance modulation of graphene monolayer. Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films, 2018, 36, 05G508.	2.1	3

#	Article	IF	Citations
19	Study of defects in Î²-Ga2O3 by isothermal capacitance transient spectroscopy. Journal of Vacuum Science and Technology B:Nanotechnology and Microelectronics, 2019, 37, 041204.	1.2	3
20	Tailoring the Potential Landscape and Electrical Properties of 2D MoS₂ using Gold Nanostructures of Different Coverage Density. Journal of Physical Chemistry C, 2020, 124, 6461-6466.	3.1	3
21	Zeeman spin-splitting in the (010) Î²-Ga2O3 two-dimensional electron gas. Applied Physics Letters, 2019, 115, .	3.3	1
22	Electrical Properties 1. Springer Series in Materials Science, 2020, , 389-405.	0.6	0